

file: g:/coursesS19/303/OTA_QvsM.mcd 03/02/19

Mathdad program to compare BJT vs MOS OTA response. Only 1st quadrant given as output current I_o is symmetric in differential input voltage v .

bias voltages: $V_{Plus} := 5$ $V_{minus} := V_{Plus}$

$I_T := 5 \cdot 10^{-3}$ $V_T := 26 \cdot 10^{-3}$ $k := 4 \cdot 10^{-3}$ $k = KP \cdot W / (2L)$ for MOS

BJT output current = $I_{oBJT}(v)$; v = differential input voltage

$$I_{oBJT}(v) := I_T \cdot \tanh\left(\frac{v}{2 \cdot V_T}\right) \quad V_B = \text{MOS break } V \text{ to } I_T \quad V_B := \sqrt{\frac{I_T}{k}} \quad V_B = 1.118$$

$$V_{scale} := \sqrt{\frac{k}{2 \cdot I_T}} \quad V_{scale} = 0.632$$

$MOS(v) := v \cdot V_{scale}$

MOS output current = $I_{oMOS}(v)$; $\Phi(\cdot)$ = unit step function; scale factor on v is V_{scale}

$$I_{oMOS}(v) := 2 \cdot I_T \cdot MOS(v) \cdot \left[\sqrt{1 - MOS(v)^2} \right] \cdot \Phi(V_B - v) + I_T \cdot \Phi(v - V_B)$$

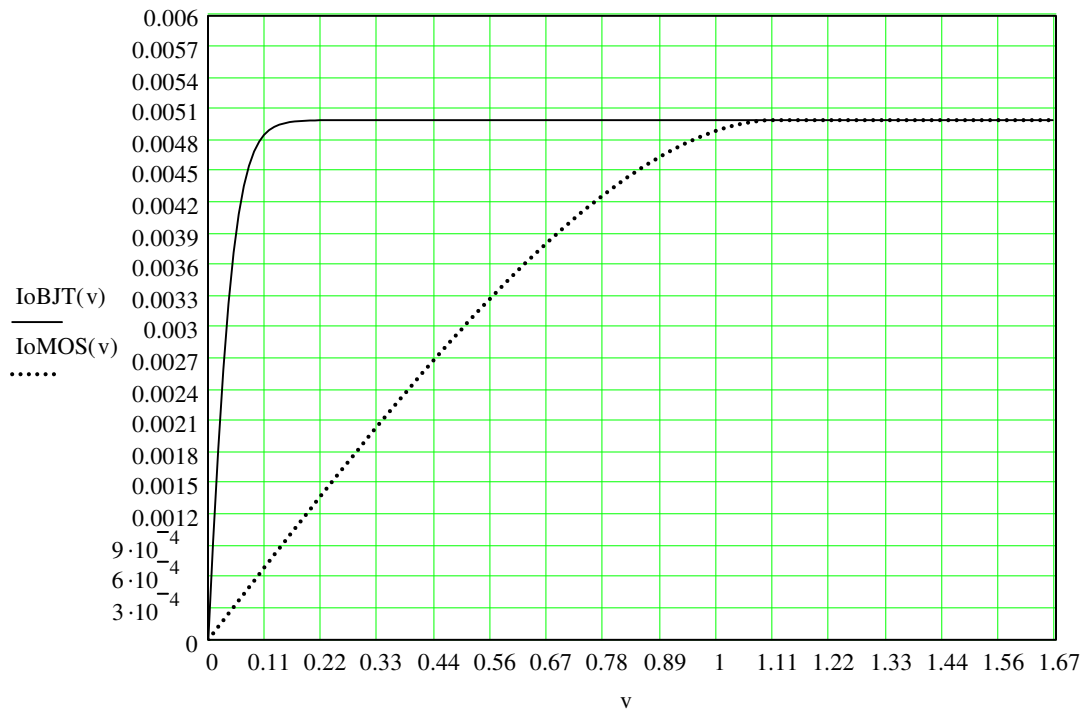
Check V_B works in both terms

$$I_{check}(v) := 2 \cdot I_T \cdot MOS(v) \cdot \left[\sqrt{1 - MOS(v)^2} \right] \quad I_{check}(V_B) = 5 \times 10^{-3}$$

Plot both I_{outs} :

$$v_{min} := 0 \quad v_{max} := \frac{V_{Plus}}{3} \quad dv := 0.01 \quad I_{max} := I_T \cdot \frac{6}{5}$$

$v := v_{min}, v_{min} + dv .. v_{max}$

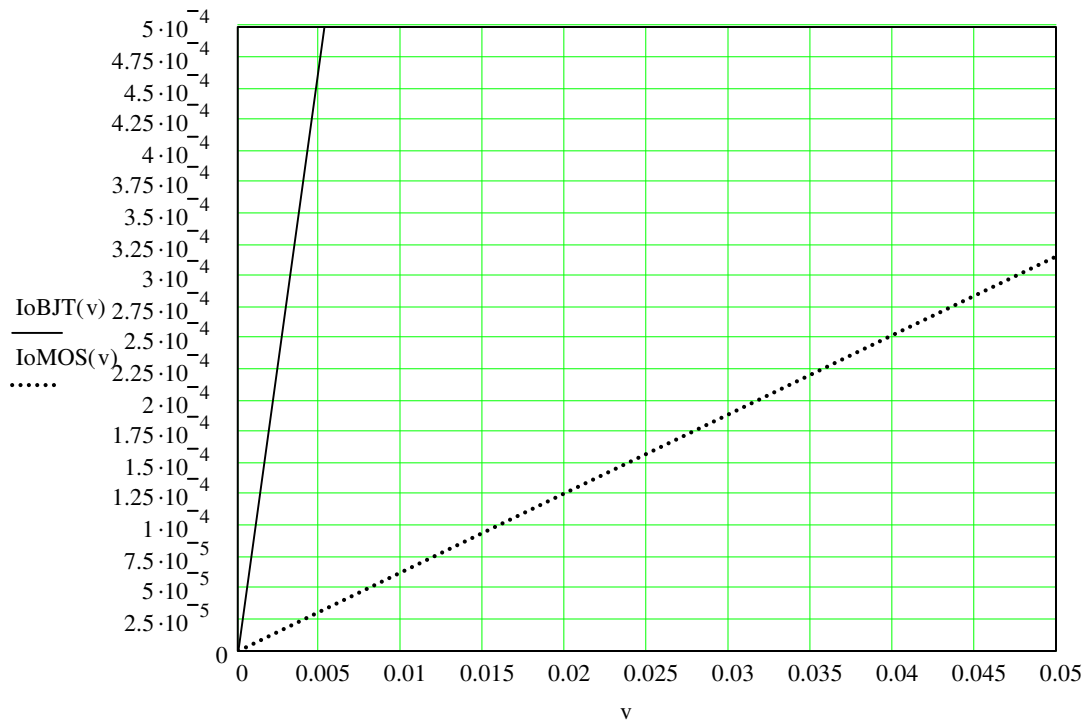


Rescale: x axis to look near origin

$$v_{\max} := \frac{V_{\text{Plus}}}{100}$$

$$dv := 0.001$$

$$I_{\max} := \frac{IT}{10}$$



Redesign MOS so both MOS and BJT have same gm at v=0 by varying IT as function of k:

Derivatives at the origin: BJT=IT/(2VT) for MOS=2ITVscale, Vscale=sqrt(k/(2IT))
 setting them equal $1=4VT\sqrt{k/(2IT)}$ or $k=2IT/16(VT^2)$

$$k_{\text{eq}}(IT) := \frac{IT}{8 \cdot VT^2}$$

$$k_{\text{eq}}(IT) = 0.925$$

$$IT_{\text{eq}}(k) := 8 \cdot k \cdot VT^2$$

$$IT_{\text{eq}}(k) = 2.163 \times 10^{-5}$$

$$\text{MOS}(v, k) := \left[\sqrt{\left(\frac{k}{2 \cdot IT_{\text{eq}}(k)} \right)} \right] \cdot v$$

$$V_B(k) := \sqrt{\frac{IT_{\text{eq}}(k)}{k}}$$

$$V_B(k) = 0.074$$

Redefine IoMOS to include function of k:

$$I_{\text{oMOS}}(v, k) := 2 \cdot IT \cdot \text{MOS}(v, k) \cdot \left[\sqrt{1 - \text{MOS}(v, k)^2} \right] \cdot \Phi(V_B(k) - v) + IT \cdot \Phi(v - V_B(k))$$

Replot to show the equal gm and comparison for non-small input v:

$$v_{\max} := \frac{V_{\text{Plus}}}{40} \quad dv := 0.01 \quad I_{\max}(k) := I_{\text{Teq}}(k) \cdot \frac{1000}{4}$$

